# Analog Power AM20N10-350D MOSFET Datasheet

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Key Features:
Low rDS(on) trench technology
Low thermal impedance
Fast switching speed
Typical Applications:
White LED boost converters
Automotive Systems
Industrial DC/DC Conversion Circuits

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## N-Channel 100-V (D-S) MOSFET

### **Key Features:**

- Low r<sub>DS(on)</sub> trench technology
- · Low thermal impedance
- · Fast switching speed

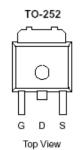
## **Typical Applications:**

- White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	$r_{DS(on)}(m\Omega)$	I <sub>D</sub> (A)		
100	420 @ V <sub>GS</sub> = 10V	9.0		
	460 @ V <sub>GS</sub> = 5.5V	8.6		







ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)						
Parameter		Symbol	Limit	Units		
Drain-Source Voltage		$V_{DS}$	100	V		
Gate-Source Voltage		$V_{GS}$	±20	V		
Continuous Drain Current a	T <sub>A</sub> =25°C	I <sub>D</sub>	9.0	Α		
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	50	^		
Continuous Source Current (Diode Conduction) <sup>a</sup>	I <sub>S</sub>	33.6	Α			
Power Dissipation <sup>a</sup>	T <sub>A</sub> =25°C	$P_{D}$	50	W		
Operating Junction and Storage Temperature Range		$T_J, T_{stg}$	-55 to 175	°C		

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Maximum	Units		
Maximum Junction-to-Ambient <sup>a</sup>	$R_{\theta JA}$	40	°C/W		
Maximum Junction-to-Case	$R_{\theta JC}$	3	C/VV		

#### Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

#### **Electrical Characteristics**

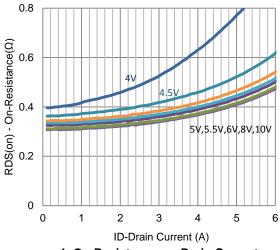
Parameter	Symbol	Symbol Test Conditions		Тур	Max	Unit
Static						
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250 \text{ uA}$	1			V
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA
Zero Gate Voltage Drain Current	1	$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}$			1	uA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			25	uA
On-State Drain Current	I <sub>D(on)</sub>	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	10			Α
Drain-Source On-Resistance	r	$V_{GS} = 10 \text{ V}, I_{D} = 5 \text{ A}$			420	mΩ
Dialii-Source Oil-Resistance	r <sub>DS(on)</sub>	$V_{GS} = 5.5 \text{ V}, I_D = 4.2 \text{ A}$			460	11177
Forward Transconductance	g <sub>fs</sub>	$V_{DS} = 15 \text{ V}, I_{D} = 5 \text{ A}$		20		S
Diode Forward Voltage	$V_{SD}$	I <sub>S</sub> = 16.8 A, V <sub>GS</sub> = 0 V		1.21		V
		Dynamic				
Total Gate Charge	$Q_g$	$V_{DS} = 50 \text{ V}, V_{GS} = 5.5 \text{ V},$		3.3		
Gate-Source Charge	$Q_{gs}$	$I_{DS} = 50 \text{ V}, V_{GS} = 5.3 \text{ V},$ $I_{D} = 5 \text{ A}$		0.9		nC
Gate-Drain Charge	$Q_{gd}$	ID = 3 A		1.9		
Turn-On Delay Time	t <sub>d(on)</sub>	$V_{DS} = 50 \text{ V}, R_1 = 10 \Omega,$		3		
Rise Time	t <sub>r</sub>	$V_{DS} = 50 \text{ V}, K_L - 10 \Omega;$ $I_D = 5 \text{ A},$		7		ne
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = 10 \text{ V}, R_{GEN} = 6 \Omega$		13		ns
Fall Time	t <sub>f</sub>	VGEN = 10 V, NGEN = 0 12		5		
Input Capacitance	C <sub>iss</sub>			176		
Output Capacitance	C <sub>oss</sub>	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		22		pF
Reverse Transfer Capacitance	$C_{rss}$	]		18		

#### Notes

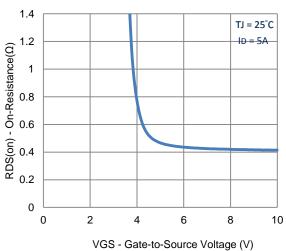
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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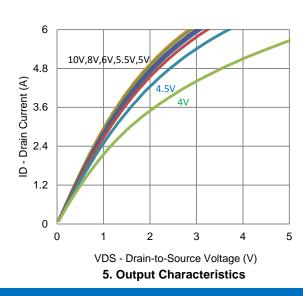
## **Typical Electrical Characteristics**



1. On-Resistance vs. Drain Current

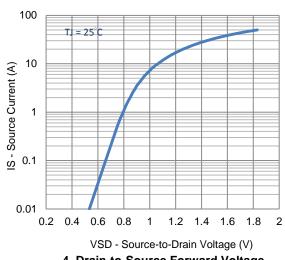


3. On-Resistance vs. Gate-to-Source Voltage

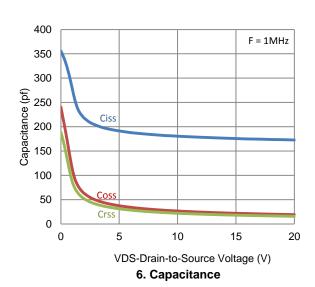


5 TJ = 25°C 4 ID - Drain Current (A) 1 0 0 1 2 6 VGS - Gate-to-Source Voltage (V)

2. Transfer Characteristics



4. Drain-to-Source Forward Voltage

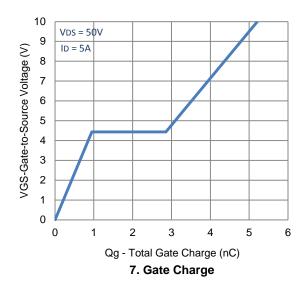


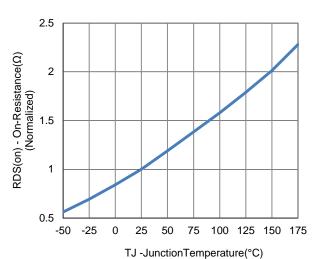
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## **Typical Electrical Characteristics**





100

10 US

100 US

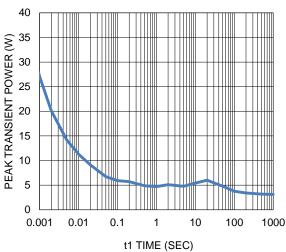
100 US

100 US

100 MS

10

8. Normalized On-Resistance Vs Junction Temperature



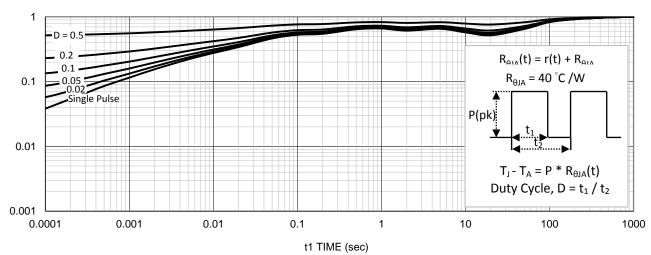
VDS Drain to Source Voltage (V)
9. Safe Operating Area

100

1000

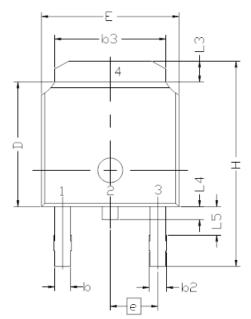
10

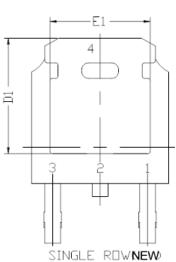
10. Single Pulse Maximum Power Dissipation

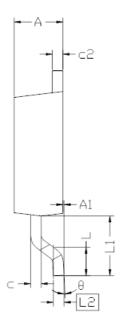


11. Normalized Thermal Transient Junction to Ambient

## **Package Information**







OVALDE	DIMENS:	[DNAL F	REQMTS			
SYMBOL	MIN	NDM	MAX			
E	6.40	6.60	6.731			
L	1.40	1.52	1.77			
L1	2.743 REF					
L2	0.	.508 BS	:C			
L3	0.89		1.27			
L4	0.64		1.01			
L5						
D	6.00	6.10	6,223			
Н	9.40	10.00	10.40			
b	0.64	0.76	0.88			
b2	0.77	0.84	1.14			
b3	5.21	5.34	5.46			
е	2.	286 BS	C			
A	2,20	2,30	2.38			
A1	0		0.127			
C	0.45	0.50	0.60			
c2	0.45	0.50	0,58			
D1	5,30					
E1	4.40					
Θ	0°		10°			

#### Note:

- 1. All Dimension Are In mm.
- Package Body Sizes Exclude Mold Flash, Protrusion Or Gate Burrs. Mold Flash, Protrusion Or Gate Burrs Shall Not Exceed 0.10 mm Per Side.
- 3. Package Body Sizes Determined At The Outermost Extremes Of The Plastic Body Exclusive Of Mold Flash, Gate Burrs And Interlead Flash, But Including Any Mismatch Between The Top And Bottom Of The Plastic Body.